

N-Channel Enhancement Mode Power MOSFET

Description

The FNK0203E-2 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications .It is ESD protested.

Schematic diagram

General Features

V_{DS} = 20V,I_D =7A

 $R_{DS(ON)} < 26 \,\mathrm{m}\Omega$ @ $V_{GS} = 2.5 \mathrm{V}$

 $R_{DS(ON)}$ <22 m Ω @ V_{GS} =4.5V

ESD Rating: 2200V HBM

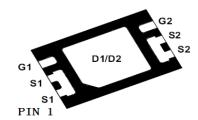
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

Application

- PWM application
- ●Load switch



Marking and pin Assignment



Absolute Maximum Ratings (TA=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	20	V	
Gate-Source Voltage	V _G s	±10	V	
Drain Current-Continuous	I _D	7	Α	
Drain Current-Pulsed (Note 1)	I _{DM}	30	Α	
Maximum Power Dissipation	P _D	1.5	W	
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	$^{\circ}$	

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ heta JA}$	83.3	°C/W
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Electrical Characteristics (TA=25℃ unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	20		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =20V,V _{GS} =0V	-	-	1	μΑ

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Gate-Body Leakage Current	I _{GSS}	$V_{GS}=\pm 10V, V_{DS}=0V$	-	-	±10	μΑ
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS},I_{D}=250\mu A$	0.55	0.7	0.95	V
Drain-Source On-State Resistance	В	V _{GS} =4.5V, I _D =6.5A	-	15	22	mΩ
	R _{DS(ON)}	V _{GS} =2.5V, I _D =5.5A	-	20	26	mΩ
Forward Transconductance	G FS	V _{DS} =5V,I _D =7A	-	20	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}	V _{DS} =10V,V _{GS} =0V, F=1.0MHz	-	970	-	PF
Output Capacitance	C _{oss}		-	160	-	PF
Reverse Transfer Capacitance	C _{rss}		-	130	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	6		nS
Turn-on Rise Time	t _r	V_{DD} =10V,R _L =1.35Ω V_{GS} =5V,R _{GEN} =3Ω	-	13		nS
Turn-Off Delay Time	t _{d(off)}		-	52		nS
Turn-Off Fall Time	t _f		-	16		nS
Total Gate Charge	Qg	V _{DS} =10V,I _D =7A, V _{GS} =4.5V	-	15		nC
Gate-Source Charge	Q_{gs}		-	0.8	-	nC
Gate-Drain Charge	Q_{gd}		-	3.2	-	nC
Drain-Source Diode Characteristics			•		-	-
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =1A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	7	Α

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

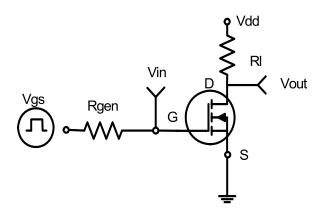


Figure 1:Switching Test Circuit

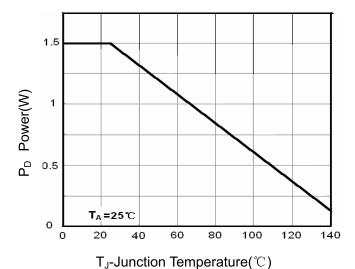


Figure 3 Power Dissipation

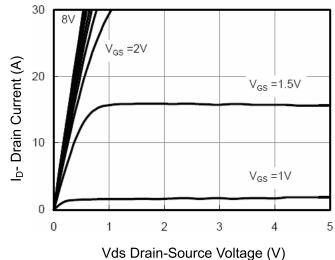


Figure 5 Output CHARACTERISTICS

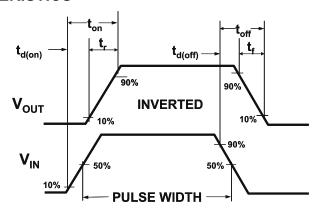


Figure 2:Switching Waveforms

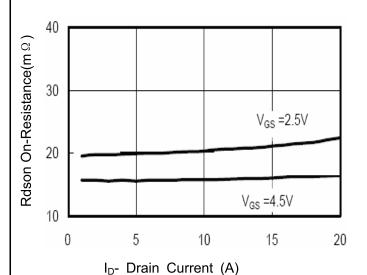


Figure 6 Drain-Source On-Resistance

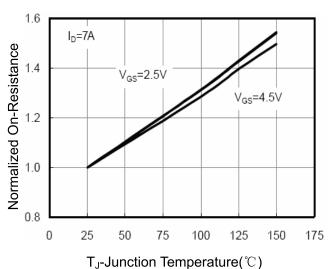


Figure 8 Drain-Source On-Resistance

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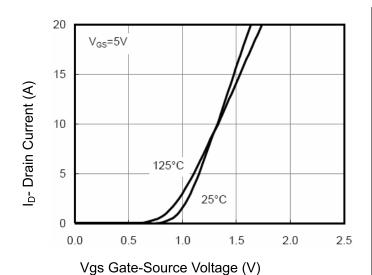
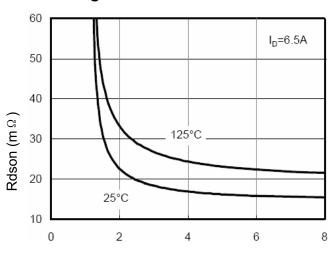
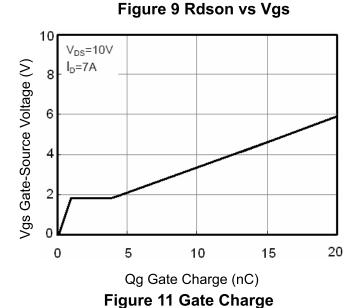


Figure 7 Transfer Characteristics



Vgs Gate-Source Voltage (V)



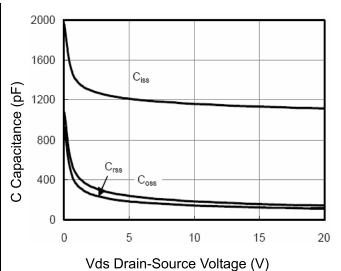


Figure 8 Capacitance vs Vds

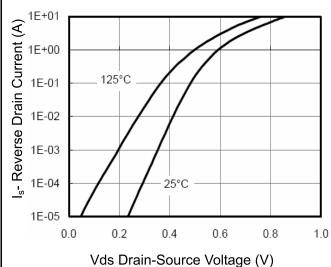


Figure 10 Capacitance vs Vds

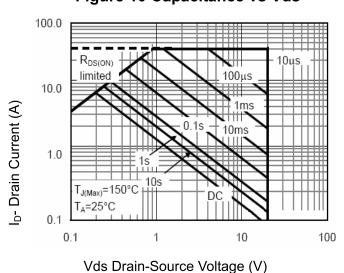


Figure 13 Safe Operation Area



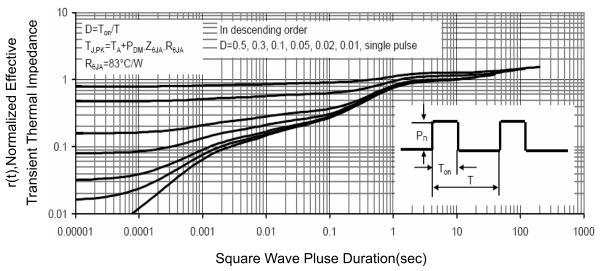
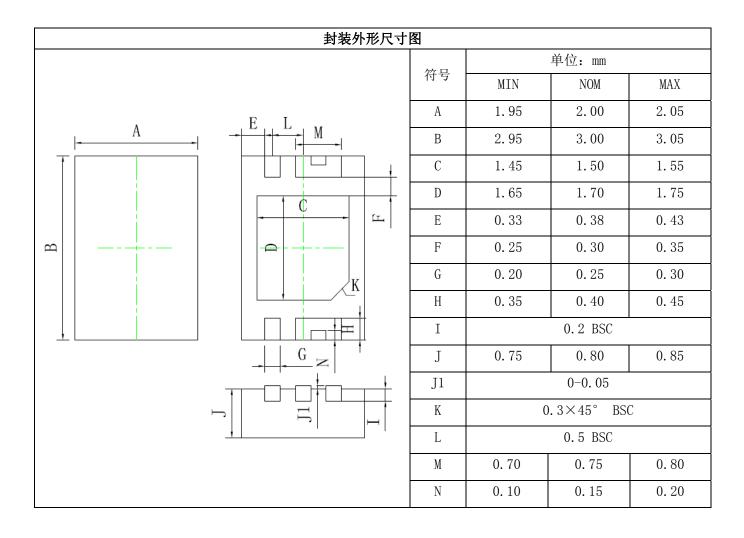


Figure 14 Normalized Maximum Transient Thermal Impedance

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